

KSD261

Low Frequency Power Amplifier

- Complement to KSA643
- Collector Power Dissipation : P_C=500mW
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



1. Emitter 2. Base 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CBO}	Collector-Base Voltage	40	V	
V _{CEO}	Collector-Emitter Voltage	20	V	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current	500	mA	
P _C	Collector Power Dissipation	500	mW	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	-55 ~ 150	°C	

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C=100\mu A, I_E=0$	40			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA, I _B =0	20			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =100μA, I _C =0	5			V
I _{CBO}	Collector Cut-off Current	V_{CB} =25V, I_{E} =0			0.1	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB}=3V$, $I_{C}=0$			0.1	μΑ
h _{FE}	DC Current Gain	V _{CE} =1V, I _C =0.1A	120		400	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =0.5A, I _B =50mA		0.18	0.4	V

$h_{\mbox{\scriptsize FE}}$ Classification

Classification	Y	G	
h _{FE}	120 ~ 240	200 ~ 400	

Typical Characteristics

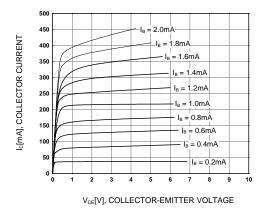


Figure 1. Static Characteristic

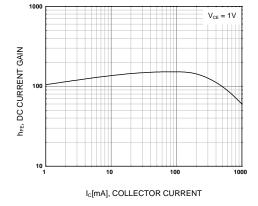


Figure 2. DC current Gain

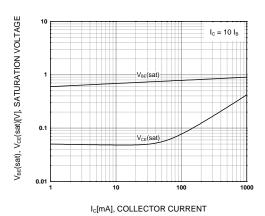


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

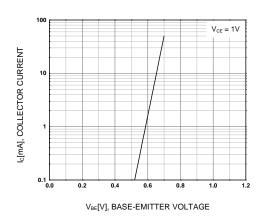


Figure 4. Base-Emitter On Voltage

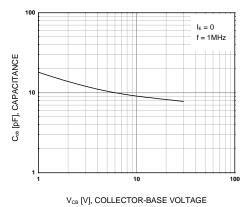
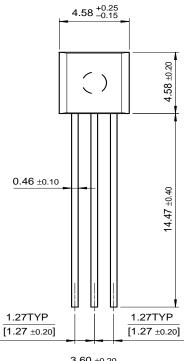


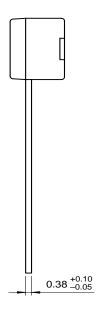
Figure 5. Collector Output Capacitance

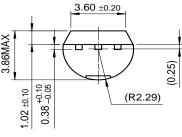
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Package Dimensions

TO-92







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